## DESCRIPTION

- With TO-220F package
- Complement to type 2SA1837
- High transition frequency

## APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

### PINNING

| PIN | DESCRIPTION |
|---|---|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

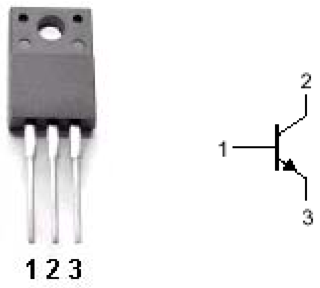

**Fig.1 simplified outline (TO-220F) and symbol**

### Absolute maximum ratings (Ta=25℃)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---|---|---|---|---|
| $V_{CBO}$ | Collector-base voltage | Open emitter | 230 | V |
| $V_{CEO}$ | Collector-emitter voltage | Open base | 230 | V |
| $V_{EBO}$ | Emitter-base voltage | Open collector | 5 | V |
| $I_C$ | Collector current | | 1 | A |
| $I_B$ | Base current | | 0.1 | A |
| $P_C$ | Collector dissipation | $T_C$=25℃ | 20 | W |
| $P_C$ | Collector dissipation | $T_a$=25℃ | 2.0 | W |
| $T_j$ | Junction temperature | | 150 | ℃ |
| $T_{stg}$ | Storage temperature | | -55~150 | ℃ |

## Silicon NPN Power Transistors 2SC4793

### CHARACTERISTICS

**Tj=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{CEO}$ | Collector-emitter breakdown voltage | $I_C$=10mA ; $I_B$=0 | 230 | | | V |
| $V_{CEsat}$ | Collector-emitter saturation voltage | $I_C$=0.5A $I_B$=50mA | | | 1.5 | V |
| $V_{BE}$ | Base-emitter voltage | $I_C$=0.5A ; $V_{CE}$=5V | | | 1.0 | V |
| $I_{CBO}$ | Collector cut-off current | $V_{CB}$=230V $I_E$=0 | | | 1.0 | μA |
| $I_{EBO}$ | Emitter cut-off current | $V_{EB}$=5V; $I_C$=0 | | | 1.0 | μA |
| $h_{FE}$ | DC current gain | $I_C$=0.1A ; $V_{CE}$=5V | 100 | | 320 | |
| $C_{OB}$ | Output capacitance | $I_E$=0; $V_{CB}$=10V;f=1MHz | | 20 | | pF |
| $f_T$ | Transition frequency | $I_C$=0.1A ; $V_{CE}$=10V | | 100 | | MHz |

## Silicon NPN Power Transistors 2SC4793

### PACKAGE OUTLINE

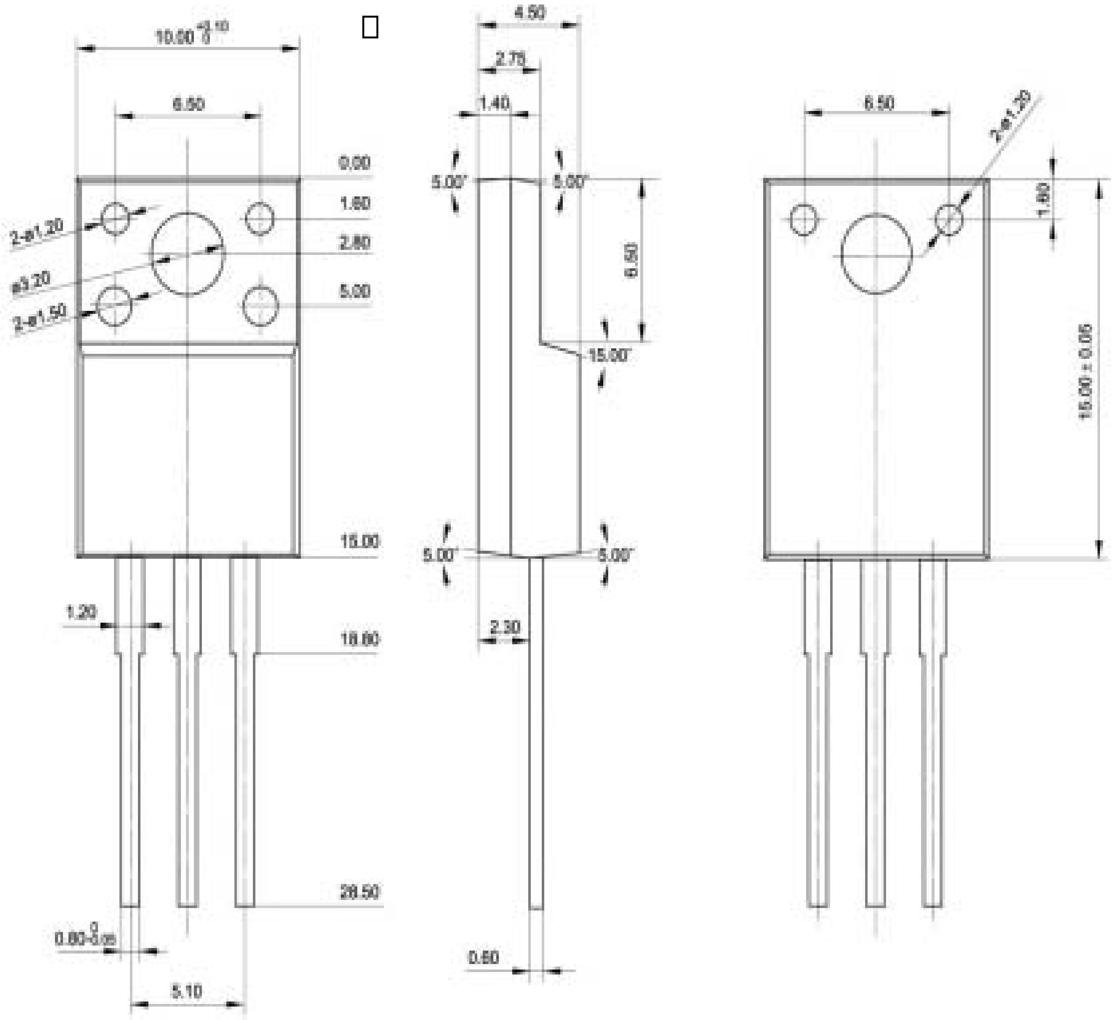

Fig.2 Outline dimensions